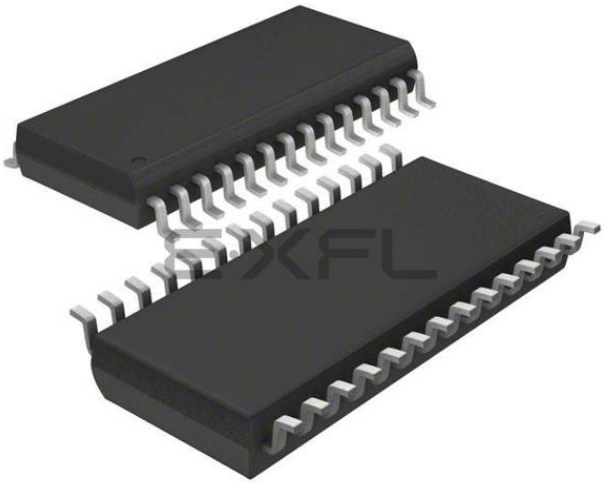

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What Are Embedded - Microcontrollers - Application Specific?

Application-specific microcontrollers are engineered to

Details	
Product Status	Active
Applications	USB Microcontroller
Core Processor	M8C
Program Memory Type	FLASH (16KB)
Controller Series	CY7C642xx
RAM Size	1K x 8
Interface	I²C, USB
Number of I/O	22
Voltage - Supply	3V ~ 5.25V
Operating Temperature	-40°C ~ 85°C
Mounting Type	Surface Mount
Package / Case	28-SSOP (0.209", 5.30mm Width)
Supplier Device Package	28-SSOP
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy7c64215-28pvxit

Applications

- PC human interface devices
  - Mouse (optomechanical, optical, trackball)
  - Keyboards
  - Joysticks
- Gaming
  - Game pads
  - Console keyboards
- General purpose
  - Barcode scanners
  - POS terminal
  - Consumer electronics
  - Toys
  - Remote controls
  - USB to serial

enCoRe III Functional Overview

The enCoRe III is based on the flexible PSoC architecture and is a full-featured, full-speed (12-Mbps) USB part. Configurable analog, digital, and interconnect circuitry enable a high level of integration in a host of consumer, and communication applications.

This architecture enables the user to create customized peripheral configurations that match the requirements of each individual application. Additionally, a fast CPU, flash program memory, SRAM data memory, and configurable I/O are included in both 28-pin SSOP and 56-pin QFN packages.

enCoRe III architecture, as illustrated in the "Block Diagram" on page 1, is comprised of four main areas: enCoRe III core, digital system, analog system, and system resources including a full-speed USB port. Configurable global busing enables all the device resources to combine into a complete custom system. The enCoRe III CY7C64215 can have up to seven I/O ports that connect to the global digital and analog interconnects, providing access to four digital blocks and six analog blocks.

enCoRe III Core

The enCoRe III Core is a powerful engine that supports a rich feature set. The core includes a CPU, memory, clocks, and configurable GPIOs.

The M8C CPU core is a powerful processor with speeds up to 24 MHz, providing a four-million instructions per second (MIPS) 8-bit Harvard-architecture microprocessor. The CPU uses an interrupt controller with up to 20 vectors, to simplify programming of real-time embedded events. Program execution is timed and protected using the included sleep and watchdog timers (WDT).

Memory encompasses 16 KB of flash for program storage, 1 KB of SRAM for data storage, and up to 2 KB of EEPROM emulated using the flash. Program flash uses four protection levels on blocks of 64 bytes, enabling customized software IP protection.

enCoRe III incorporates flexible internal clock generators, including a 24-MHz internal main oscillator (IMO) accurate to 8% over temperature and voltage as well as an option for an external clock oscillator (ECO). USB operation requires the OSC LOCK bit of the USB_CR0 register to be set to obtain IMO accuracy to.25%.

The 24-MHz IMO is doubled to 48 MHz for use by the digital system, if needed. The 48-MHz clock is required to clock the USB block and must be enabled for communication. A low-power 32-kHz internal low-speed oscillator (ILO) is provided for the sleep timer and WDT. The clocks, together with programmable clock dividers (system resource), provide flexibility to integrate almost any timing requirement into enCoRe III. In USB systems, the IMO self-tunes to ±0.25% accuracy for USB communication.

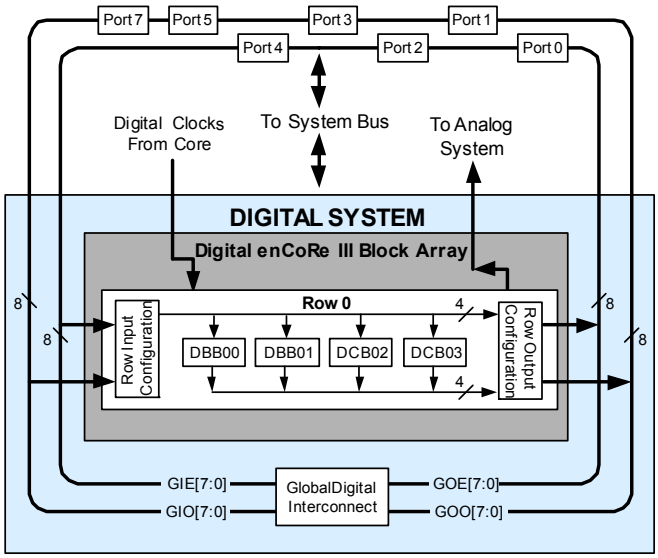
The extended temperature range for the industrial operating range (–40 °C to +85 °C) requires the use of an ECO, which is only available on the 56-pin QFN package.

enCoRe III GPIOs provide connection to the CPU, digital and analog resources of the device. Each pin's drive mode may be selected from eight options, enabling great flexibility in external interfacing. Every pin also has capability to generate a system interrupt on high-level, low-level, and change from last read.

The Digital System

The digital system is composed of four digital enCoRe III blocks. Each block is an 8-bit resource that is used alone or combined with other blocks to form 8-, 16-, 24-, and 32-bit peripherals, which are called user module references.

Figure 1. Digital System Block Diagram



The following digital configurations can be built from the blocks:

- PWMs, timers, and counters (8-bit and 16-bit)
- UART 8-bit with selectable parity
- SPI master and slave
- I^2C master
- RF interface: Interface to Cypress CYFI radio

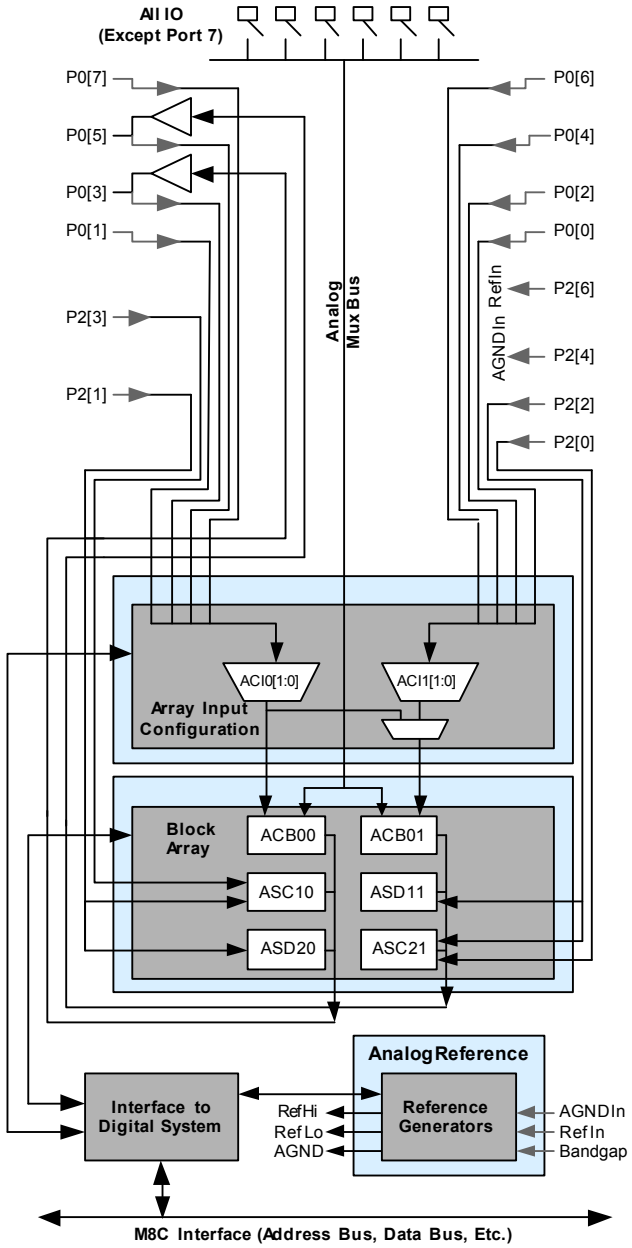
The digital blocks are connected to any GPIO through a series of global buses that can route any signal to any pin. The buses also enable signal multiplexing and performing logic operations. This configurability frees your designs from the constraints of a fixed peripheral controller.

The Analog System

The analog system is composed of six configurable blocks, comprised of an opamp circuit enabling the creation of complex analog signal flows. Analog peripherals are very flexible and are customized to support specific application requirements. enCoRe III analog function supports the Analog-to-digital converters (with 6- to 14-bit resolution, selectable as incremental, and delta-sigma) and programmable threshold comparator).

Analog blocks are arranged in two columns of three, with each column comprising one continuous time (CT) - AC B00 or AC B01 - and two switched capacitor (SC) - ASC10 and ASD20 or ASD11 and ASC21 - blocks, as shown in Figure 2.

Figure 2. Analog System Block Diagram



The Analog Multiplexer System

The analog mux bus can connect to every GPIO pin in ports 0 to 5. Pins are connected to the bus individually or in any combination. The bus also connects to the analog system for analysis with comparators and analog-to-digital converters. It is split into two sections for simultaneous dual-channel processing. An additional 8:1 analog input multiplexer provides a second path to bring Port 0 pins to the analog array.

Additional System Resources

System resources provide additional capability useful to complete systems. Additional resources include a multiplier, decimator, low voltage detection, and power-on reset. Brief statements describing the merits of each resource follow.

- Full-speed USB (12 Mbps) with five configurable endpoints and 256 bytes of RAM. No external components required except two series resistors. Industrial temperature operating range for USB requires an external clock oscillator.
- Two multiply accumulates (MACs) provide fast 8-bit multipliers with 32-bit accumulate, to assist in both general math and digital filters.
- The decimator provides a custom hardware filter for digital signal processing applications including the creation of delta-sigma ADCs.
- Digital clock dividers provide three customizable clock frequencies for use in applications. The clocks are routed to both the digital and analog systems.
- The I^2C module provides 100- and 400-kHz communication over two wires. Slave, master, and multimaster modes are all supported.
- LVD interrupts can signal the application of falling voltage levels, while the advanced power-on reset (POR) circuit eliminates the need for a system supervisor.

enCoRe III Device Characteristics

enCoRe III devices have four digital blocks and six analog blocks. The following table lists the resources available for specific enCoRe III devices.

Table 1. enCoRe III Device Characteristics

Part Number	Digital I/O	Digital Rows	Digital Blocks	Analog Inputs	Analog Outputs	Analog Columns	Analog Blocks	SRAM Size	Flash Size
CY7C64215 28 Pin	up to 22	1	4	22	2	2	6	1K	16K
CY7C64215 56 Pin	up to 50	1	4	48	2	2	6	1K	16K

Pin Information

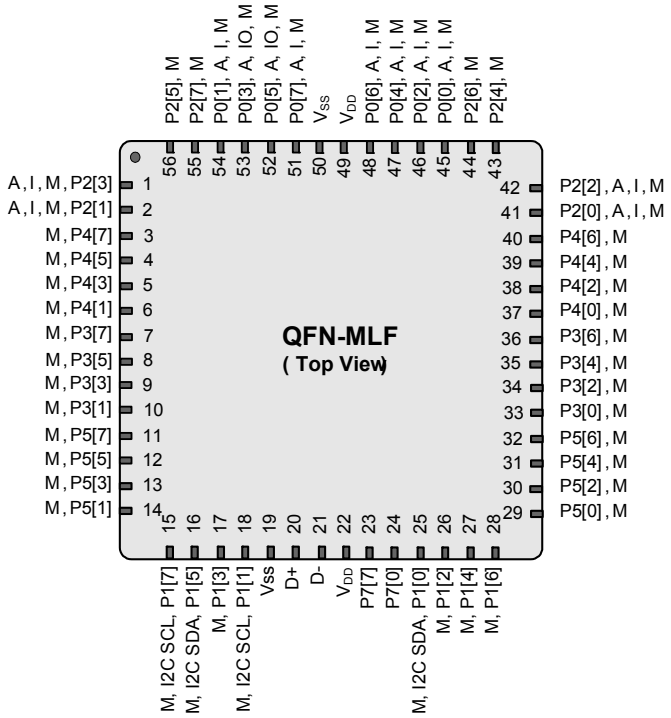
56-Pin Part Pinout

The CY7C64215 enCoRe III device is available in a 56-pin package which is listed and illustrated in the following table. Every port pin (labeled “P”) is capable of digital I/O. However, V_{SS} and V_{DD} are not capable of digital I/O.

Table 2. 56-Pin Part Pinout (QFN-MLF SAWN)[1]

Pin No.	Type		Name	Description
	Digital	Analog		
1	I/O	I, M	P2[3]	Direct switched capacitor block input.
2	I/O	I, M	P2[1]	Direct switched capacitor block input.
3	I/O	M	P4[7]	
4	I/O	M	P4[5]	
5	I/O	M	P4[3]	
6	I/O	M	P4[1]	
7	I/O	M	P3[7]	
8	I/O	M	P3[5]	
9	I/O	M	P3[3]	
10	I/O	M	P3[1]	
11	I/O	M	P5[7]	
12	I/O	M	P5[5]	
13	I/O	M	P5[3]	
14	I/O	M	P5[1]	
15	I/O	M	P1[7]	I^2C serial clock (SCL).
16	I/O	M	P1[5]	I^2C serial data (SDA).
17	I/O	M	P1[3]	
18	I/O	M	P1[1]	I^2C SCL, ISSP-SCLK.
19	Power		V_{SS}	Ground connection.
20	USB		D+	
21	USB		D-	
22	Power		V_{DD}	Supply voltage.
23	I/O		P7[7]	
24	I/O		P7[0]	
25	I/O	M	P1[0]	I^2C SDA, ISSP-SDATA.
26	I/O	M	P1[2]	
27	I/O	M	P1[4]	Optional external clock input EXTCLK.
28	I/O	M	P1[6]	
29	I/O	M	P5[0]	
30	I/O	M	P5[2]	
31	I/O	M	P5[4]	
32	I/O	M	P5[6]	
33	I/O	M	P3[0]	
34	I/O	M	P3[2]	
35	I/O	M	P3[4]	
36	I/O	M	P3[6]	
37	I/O	M	P4[0]	
38	I/O	M	P4[2]	
39	I/O	M	P4[4]	
40	I/O	M	P4[6]	
41	I/O	I, M	P2[0]	Direct switched capacitor block input.
42	I/O	I, M	P2[2]	Direct switched capacitor block input.
43	I/O	M	P2[4]	External analog ground (AGND) input.
44	I/O	M	P2[6]	External voltage reference (VREF) input.
45	I/O	I, M	P0[0]	Analog column mux input.
46	I/O	I, M	P0[2]	Analog column mux input and column output.
47	I/O	I, M	P0[4]	Analog column mux input and column output.
48	I/O	I, M	P0[6]	Analog column mux input.
49	Power		V_{DD}	Supply voltage.
50	Power		V_{SS}	Ground connection.
51	I/O	I, M	P0[7]	Analog column mux input.
52	I/O	I/O, M	P0[5]	Analog column mux input and column output
53	I/O	I/O, M	P0[3]	Analog column mux input and column output.
54	I/O	I, M	P0[1]	Analog column mux input.
55	I/O	M	P2[7]	
56	I/O	M	P2[5]	

Figure 3. CY7C64215 56-Pin enCoRe III Device



LEGEND A = Analog, I = Input, O = Output, and M = Analog Mux Input.

Note
1. The center pad on the QFN-MLF package should be connected to ground (V_{SS}) for best mechanical, thermal, and electrical performance. If not connected to ground, it should be electrically floated and not connected to any other signal.

Register Map Bank 0 Table: User Space

Name	Addr (0,Hex)	Access	Name	Addr (0,Hex)	Access	Name	Addr (0,Hex)	Access	Name	Addr (0,Hex)	Access
PRT0DR	00	RW	PMA0_DR	40	RW	ASC10CR0	80	RW		C0	
PRT0IE	01	RW	PMA1_DR	41	RW	ASC10CR1	81	RW		C1	
PRT0GS	02	RW	PMA2_DR	42	RW	ASC10CR2	82	RW		C2	
PRT0DM2	03	RW	PMA3_DR	43	RW	ASC10CR3	83	RW		C3	
PRT1DR	04	RW	PMA4_DR	44	RW	ASD11CR0	84	RW		C4	
PRT1IE	05	RW	PMA5_DR	45	RW	ASD11CR1	85	RW		C5	
PRT1GS	06	RW	PMA6_DR	46	RW	ASD11CR2	86	RW		C6	
PRT1DM2	07	RW	PMA7_DR	47	RW	ASD11CR3	87	RW		C7	
PRT2DR	08	RW	USB_SOF0	48	R		88			C8	
PRT2IE	09	RW	USB_SOF1	49	R		89			C9	
PRT2GS	0A	RW	USB_CR0	4A	RW		8A			CA	
PRT2DM2	0B	RW	USBIO_CR0	4B	#		8B			CB	
PRT3DR	0C	RW	USBIO_CR1	4C	RW		8C			CC	
PRT3IE	0D	RW		4D			8D			CD	
PRT3GS	0E	RW	EP1_CNT1	4E	#		8E			CE	
PRT3DM2	0F	RW	EP1_CNT	4F	RW		8F			CF	
PRT4DR	10	RW	EP2_CNT1	50	#	ASD20CR0	90	RW	CUR_PP	D0	RW
PRT4IE	11	RW	EP2_CNT	51	RW	ASD20CR1	91	RW	STK_PP	D1	RW
PRT4GS	12	RW	EP3_CNT1	52	#	ASD20CR2	92	RW		D2	
PRT4DM2	13	RW	EP3_CNT	53	RW	ASD20CR3	93	RW	IDX_PP	D3	RW
PRT5DR	14	RW	EP4_CNT1	54	#	ASC21CR0	94	RW	MVR_PP	D4	RW
PRT5IE	15	RW	EP4_CNT	55	RW	ASC21CR1	95	RW	MVW_PP	D5	RW
PRT5GS	16	RW	EP0_CR	56	#	ASC21CR2	96	RW	I2C_CFG	D6	RW
PRT5DM2	17	RW	EP0_CNT	57	#	ASC21CR3	97	RW	I2C_SCR	D7	#
	18		EP0_DR0	58	RW		98		I2C_DR	D8	RW
	19		EP0_DR1	59	RW		99		I2C_MSCR	D9	#
	1A		EP0_DR2	5A	RW		9A		INT_CLR0	DA	RW
	1B		EP0_DR3	5B	RW		9B		INT_CLR1	DB	RW
PRT7DR	1C	RW	EP0_DR4	5C	RW		9C		INT_CLR2	DC	RW
PRT7IE	1D	RW	EP0_DR5	5D	RW		9D		INT_CLR3	DD	RW
PRT7GS	1E	RW	EP0_DR6	5E	RW		9E		INT_MSK3	DE	RW
PRT7DM2	1F	RW	EP0_DR7	5F	RW		9F		INT_MSK2	DF	RW
DBB00DR0	20	#	AMX_IN	60	RW		A0		INT_MSK0	E0	RW
DBB00DR1	21	W	AMUXCFG	61	RW		A1		INT_MSK1	E1	RW
DBB00DR2	22	RW		62			A2		INT_VC	E2	RC
DBB00CR0	23	#	ARF_CR	63	RW		A3		RES_WDT	E3	W
DBB01DR0	24	#	CMP_CR0	64	#		A4		DEC_DH	E4	RC
DBB01DR1	25	W	ASY_CR	65	#		A5		DEC_DL	E5	RC
DBB01DR2	26	RW	CMP_CR1	66	RW		A6		DEC_CR0	E6	RW
DBB01CR0	27	#		67			A7		DEC_CR1	E7	RW
DCB02DR0	28	#		68		MUL1_X	A8	W	MUL0_X	E8	W
DCB02DR1	29	W		69		MUL1_Y	A9	W	MUL0_Y	E9	W
DCB02DR2	2A	RW		6A		MUL1_DH	AA	R	MUL0_DH	EA	R
DCB02CR0	2B	#		6B		MUL1_DL	AB	R	MUL0_DL	EB	R
DCB03DR0	2C	#	TMP_DR0	6C	RW	ACC1_DR1	AC	RW	ACC0_DR1	EC	RW
DCB03DR1	2D	W	TMP_DR1	6D	RW	ACC1_DR0	AD	RW	ACC0_DR0	ED	RW
DCB03DR2	2E	RW	TMP_DR2	6E	RW	ACC1_DR3	AE	RW	ACC0_DR3	EE	RW
DCB03CR0	2F	#	TMP_DR3	6F	RW	ACC1_DR2	AF	RW	ACC0_DR2	EF	RW
	30		ACB00CR3	70	RW	RDI0RI	B0	RW		F0	
	31		ACB00CR0	71	RW	RDI0SYN	B1	RW		F1	
	32		ACB00CR1	72	RW	RDI0IS	B2	RW		F2	
	33		ACB00CR2	73	RW	RDI0LT0	B3	RW		F3	
	34		ACB01CR3	74	RW	RDI0LT1	B4	RW		F4	
	35		ACB01CR0	75	RW	RDI0RO0	B5	RW		F5	
	36		ACB01CR1	76	RW	RDI0RO1	B6	RW		F6	
	37		ACB01CR2	77	RW		B7		CPU_F	F7	RL
	38			78			B8			F8	
	39			79			B9			F9	
	3A			7A			BA			FA	
	3B			7B			BB			FB	
	3C			7C			BC			FC	
	3D			7D			BD		DAC_D	FD	RW
	3E			7E			BE		CPU_SCR1	FE	#
	3F			7F			BF		CPU_SCR0	FF	#

Blank fields are Reserved and should not be accessed.

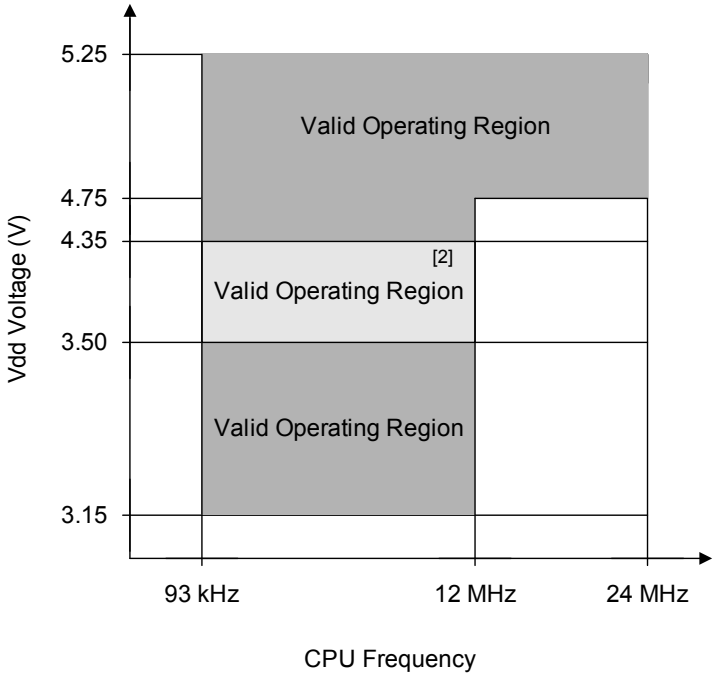
Access is bit specific.

Electrical Specifications

This section presents the DC and AC electrical specifications of the CY7C64215 enCoRe III. For the most up-to-date electrical specifications, confirm that you have the most recent datasheet by going to the web at http://www.cypress.com/go/usb.

Specifications are valid for –40 °C ≤ T_A ≤ 85 °C and T_J ≤ 100 °C, except where noted. Specifications for devices running at greater than 12 MHz are valid for –40 °C ≤ T_A ≤ 70°C and T_J ≤ 82 °C.

Figure 5. Voltage versus CPU Frequency



Note
2. This is a valid operating region for the CPU, but USB hardware is non functional in the voltage range from 3.50 V to 4.35 V.

DC Electrical Characteristics

DC Chip-Level Specifications

The following table lists guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and –40 °C ≤ T_A ≤ 85 °C, or 3.15 V to 3.5 V and –40 °C ≤ T_A ≤ 85 °C, respectively. Typical parameters apply to 5 V and 3.3 V at 25 °C and are for design guidance only.

Table 7. DC Chip-Level Specifications

Parameter	Description	Min	Typ	Max	Unit	Notes
V_{DD}	Supply voltage	3.0	–	5.25	V	See DC POR and LVD specifications, Table 15 on page 22. USB hardware is not functional when V_{DD} is between 3.5 V to 4.35 V.
I_{DD5}	Supply current, IMO = 24 MHz (5 V)	–	14	27	mA	Conditions are V_{DD} = 5.0 V, T_A = 25 °C, CPU = 3 MHz, SYSCLK doubler disabled, VC1 = 1.5 MHz, VC2 = 93.75 kHz, VC3 = 93.75 kHz, analog power = off.
I_{DD3}	Supply current, IMO = 24 MHz (3.3 V)	–	8	14	mA	Conditions are V_{DD} = 3.3 V, T_A = 25 °C, CPU = 3 MHz, SYSCLK doubler disabled, VC1 = 1.5 MHz, VC2 = 93.75 kHz, VC3 = 0.367 kHz, analog power = off.
I_{SB}	Sleep [3] (mode) current with POR, LVD, sleep timer, and WDT [4].	–	3	6.5	µA	Conditions are with internal slow speed oscillator, V_{DD} = 3.3 V, 0 °C ≤ T_A ≤ 55 °C, analog power = off.
I_{SBH}	Sleep (mode) current with POR, LVD, sleep timer, and WDT at high temperature [4] .	–	4	25	µA	Conditions are with internal slow speed oscillator, V_{DD} = 3.3 V, 55 °C < T_A ≤ 70 °C, analog power = off.

Notes

3. Errata: When the device operates at4.75 V to 5.25 V and the 3.3-V regulator is enabled, a short low pulse may be created on the DP signal line during device wakeup. The 15- to 20-µs low pulse of the DP line may be interpreted by the host computer as a deattach or the beginning of a wakeup. For more details refer to Errata on page 40.
4. Standby current includes all functions (POR, LVD, WDT, sleep time) needed for reliable system operation. This should be compared with devices that have similar functions enabled.

DC Analog Output Buffer Specifications

The following tables list guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and –40 °C ≤ T_A ≤ 85 °C, or 3.15 V to 3.5 V and –40 °C ≤ T_A ≤ 85 °C, respectively. Typical parameters apply to 5 V and 3.3 V at 25 °C and are for design guidance only.

Table 10. 5 V DC Analog Output Buffer Specifications

Parameter	Description	Min	Typ	Max	Unit	Notes
C_L	Load Capacitance	–	–	200	pF	This specification applies to the external circuit that is being driven by the analog output buffer.
V_{OSOB}	Input offset voltage (absolute value)	–	3	12	mV	–
TCV_{OSOB}	Average input offset voltage drift	–	+6	–	µV/°C	–
V_{CMOB}	Common mode input voltage range	0.5	–	V_{DD} – 1.0	V	–
R_{OUTOB}	Output resistance Power = low Power = high	 – –	 0.6 0.6	 – –	 W W	–
$V_{OHIGHOB}$	High output voltage swing (Load = 32 ohms to $V_{DD}/2$) Power = low Power = high	 0.5 × V_{DD} + 1.1 0.5 × V_{DD} + 1.1	 – –	 – –	 V V	–
V_{OLOWOB}	Low output voltage swing (Load = 32 ohms to $V_{DD}/2$) Power = low Power = high	 – –	 – –	 0.5 × V_{DD} – 1.3 0.5 × V_{DD} – 1.3	 V V	–
I_{SOB}	Supply current including bias cell (no load) Power = low Power = high	 – –	 1.1 2.6	 5.1 8.8	 mA mA	–
$PSRR_{OB}$	Supply voltage rejection ratio	53	64	–	dB	(0.5 × V_{DD} – 1.3) ≤ V_{OUT} ≤ (V_{DD} – 2.3).

Table 11. 3.3 V DC Analog Output Buffer Specifications

Parameter	Description	Min	Typ	Max	Unit	Notes
C_L	Load Capacitance	–	–	200	pF	This specification applies to the external circuit that is being driven by the analog output buffer.
V_{OSOB}	Input offset voltage (absolute value)	–	3	12	mV	–
TCV_{OSOB}	Average input offset voltage drift	–	+6	–	µV/°C	–
V_{CMOB}	Common mode input voltage range	0.5	-	V_{DD} – 1.0	V	–
R_{OUTOB}	Output resistance Power = low Power = high	 – –	 1 1	 – –	 W W	–
$V_{OHIGHOB}$	High output voltage swing (Load = 1 KΩ to $V_{DD}/2$) Power = low Power = high	 0.5 × V_{DD} + 1.0 0.5 × V_{DD} + 1.0	 – –	 – –	 V V	–
V_{OLOWOB}	Low output voltage swing (Load = 1 KΩ to $V_{DD}/2$) Power = low Power = high	 – –	 – –	 0.5 × V_{DD} – 1.0 0.5 × V_{DD} – 1.0	 V V	–
I_{SOB}	Supply current including bias cell (no load) Power = low Power = high	 –	 0.8 2.0	 2.0 4.3	 mA mA	–
$PSRR_{OB}$	Supply voltage rejection ratio	34	64	–	dB	(0.5 × V_{DD} – 1.0) ≤ V_{OUT} ≤ (0.5 × V_{DD} + 0.9).

DC Analog Reference Specifications

The following tables list guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and –40 °C ≤ T_A ≤ 85 °C, or 3.15 V to 3.5 V and –40 °C ≤ T_A ≤ 85 °C, respectively. Typical parameters apply to 5 V and 3.3 V at 25 °C and are for design guidance only.

The guaranteed specifications are measured through the analog continuous time PSoC blocks. The power levels for AGND refer to the power of the Analog Continuous Time PSoC block. The power levels for RefHi and RefLo refer to the Analog Reference Control register. The limits stated for AGND include the offset error of the AGND buffer local to the Analog Continuous Time PSoC block. Reference control power is high.

Table 12. 5-V DC Analog Reference Specifications

Reference ARF_CR [5:3]	Reference Power Settings	Symbol	Reference	Description	Min	Typ	Max	Units
0b000	RefPower = high Opamp bias = high	V_{REFHI}	Ref High	$V_{DD}/2$ + Bandgap	$V_{DD}/2$ + 1.229	$V_{DD}/2$ + 1.290	$V_{DD}/2$ + 1.346	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.038	$V_{DD}/2$	$V_{DD}/2$ + 0.040	V
		V_{REFLO}	Ref Low	$V_{DD}/2$ – Bandgap	$V_{DD}/2$ – 1.356	$V_{DD}/2$ – 1.295	$V_{DD}/2$ – 1.218	V
	RefPower = high Opamp bias = low	V_{REFHI}	Ref High	$V_{DD}/2$ + Bandgap	$V_{DD}/2$ + 1.220	$V_{DD}/2$ + 1.292	$V_{DD}/2$ + 1.348	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.036	$V_{DD}/2$	$V_{DD}/2$ + 0.036	V
		V_{REFLO}	Ref Low	$V_{DD}/2$ – Bandgap	$V_{DD}/2$ – 1.357	$V_{DD}/2$ – 1.297	$V_{DD}/2$ – 1.225	V
	RefPower = medium Opamp bias = high	V_{REFHI}	Ref High	$V_{DD}/2$ + Bandgap	$V_{DD}/2$ + 1.221	$V_{DD}/2$ + 1.293	$V_{DD}/2$ + 1.351	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.036	$V_{DD}/2$	$V_{DD}/2$ + 0.036	V
		V_{REFLO}	Ref Low	$V_{DD}/2$ – Bandgap	$V_{DD}/2$ – 1.357	$V_{DD}/2$ – 1.298	$V_{DD}/2$ – 1.228	V
	RefPower = medium Opamp bias = low	V_{REFHI}	Ref High	$V_{DD}/2$ + Bandgap	$V_{DD}/2$ + 1.219	$V_{DD}/2$ + 1.293	$V_{DD}/2$ + 1.353	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.037	$V_{DD}/2$ – 0.001	$V_{DD}/2$ + 0.036	V
		V_{REFLO}	Ref Low	$V_{DD}/2$ – Bandgap	$V_{DD}/2$ – 1.359	$V_{DD}/2$ – 1.299	$V_{DD}/2$ – 1.229	V
0b001	RefPower = high Opamp bias = high	V_{REFHI}	Ref High	P2[4]+P2[6] (P2[4] = $V_{DD}/2$, P2[6] = 1.3 V)	P2[4] + P2[6] – 0.092	P2[4] + P2[6] – 0.011	P2[4] + P2[6] + 0.064	V
		V_{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V_{REFLO}	Ref Low	P2[4]–P2[6] (P2[4] = $V_{DD}/2$, P2[6] = 1.3 V)	P2[4] – P2[6] – 0.031	P2[4] – P2[6] + 0.007	P2[4] – P2[6] + 0.056	V
	RefPower = high Opamp bias = low	V_{REFHI}	Ref High	P2[4]+P2[6] (P2[4] = $V_{DD}/2$, P2[6] = 1.3 V)	P2[4] + P2[6] – 0.078	P2[4] + P2[6] – 0.008	P2[4] + P2[6] + 0.063	V
		V_{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V_{REFLO}	Ref Low	P2[4]–P2[6] (P2[4] = $V_{DD}/2$, P2[6] = 1.3 V)	P2[4] – P2[6] – 0.031	P2[4] – P2[6] + 0.004	P2[4] – P2[6] + 0.043	V
	RefPower = medium Opamp bias = high	V_{REFHI}	Ref High	P2[4]+P2[6] (P2[4] = $V_{DD}/2$, P2[6] = 1.3 V)	P2[4] + P2[6] – 0.073	P2[4] + P2[6] – 0.006	P2[4] + P2[6] + 0.062	V
		V_{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V_{REFLO}	Ref Low	P2[4]–P2[6] (P2[4] = $V_{DD}/2$, P2[6] = 1.3 V)	P2[4] – P2[6] – 0.032	P2[4] – P2[6] + 0.003	P2[4] – P2[6] + 0.038	V
	RefPower = medium Opamp bias = low	V_{REFHI}	Ref High	P2[4]+P2[6] (P2[4] = $V_{DD}/2$, P2[6] = 1.3 V)	P2[4] + P2[6] – 0.073	P2[4] + P2[6] – 0.006	P2[4] + P2[6] + 0.062	V
		V_{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V_{REFLO}	Ref Low	P2[4]–P2[6] (P2[4] = $V_{DD}/2$, P2[6] = 1.3 V)	P2[4] – P2[6] – 0.034	P2[4] – P2[6] + 0.002	P2[4] – P2[6] + 0.037	V

Table 12. 5-V DC Analog Reference Specifications (continued)

Reference ARF_CR [5:3]	Reference Power Settings	Symbol	Reference	Description	Min	Typ	Max	Units
0b010	RefPower = high Opamp bias = high	V_{REFHI}	Ref High	V_{DD}	V_{DD} – 0.037	V_{DD} – 0.007	V_{DD}	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.036	$V_{DD}/2$ – 0.001	$V_{DD}/2$ + 0.036	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.005	V_{SS} + 0.029	V
	RefPower = high Opamp bias = low	V_{REFHI}	Ref High	V_{DD}	V_{DD} – 0.034	V_{DD} – 0.006	V_{DD}	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.036	$V_{DD}/2$ – 0.001	$V_{DD}/2$ + 0.035	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.004	V_{SS} + 0.024	V
	RefPower = medium Opamp bias = high	V_{REFHI}	Ref High	V_{DD}	V_{DD} – 0.032	V_{DD} – 0.005	V_{DD}	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.036	$V_{DD}/2$ – 0.001	$V_{DD}/2$ + 0.035	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.003	V_{SS} + 0.022	V
	RefPower = medium Opamp bias = low	V_{REFHI}	Ref High	V_{DD}	V_{DD} – 0.031	V_{DD} – 0.005	V_{DD}	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.037	$V_{DD}/2$ – 0.001	$V_{DD}/2$ + 0.035	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.003	V_{SS} + 0.020	V
0b011	RefPower = high Opamp bias = high	V_{REFHI}	Ref High	3 × Bandgap	3.760	3.884	4.006	V
		V_{AGND}	AGND	2 × Bandgap	2.522	2.593	2.669	V
		V_{REFLO}	Ref Low	Bandgap	1.252	1.299	1.342	V
	RefPower = high Opamp bias = low	V_{REFHI}	Ref High	3 × Bandgap	3.766	3.887	4.010	V
		V_{AGND}	AGND	2 × Bandgap	2.523	2.594	2.670	V
		V_{REFLO}	Ref Low	Bandgap	1.252	1.297	1.342	V
	RefPower = medium Opamp bias = high	V_{REFHI}	Ref High	3 × Bandgap	3.769	3.888	4.013	V
		V_{AGND}	AGND	2 × Bandgap	2.523	2.594	2.671	V
		V_{REFLO}	Ref Low	Bandgap	1.251	1.296	1.343	V
	RefPower = medium Opamp bias = low	V_{REFHI}	Ref High	3 × Bandgap	3.769	3.889	4.015	V
		V_{AGND}	AGND	2 × Bandgap	2.523	2.595	2.671	V
		V_{REFLO}	Ref Low	Bandgap	1.251	1.296	1.344	V
0b100	RefPower = high Opamp bias = high	V_{REFHI}	Ref High	2 × Bandgap + P2[6] (P2[6] = 1.3 V)	2.483 – P2[6]	2.582 – P2[6]	2.674 – P2[6]	V
		V_{AGND}	AGND	2 × Bandgap	2.522	2.593	2.669	V
		V_{REFLO}	Ref Low	2 × Bandgap – P2[6] (P2[6] = 1.3 V)	2.524 – P2[6]	2.600 – P2[6]	2.676 – P2[6]	V
	RefPower = high Opamp bias = low	V_{REFHI}	Ref High	2 × Bandgap + P2[6] (P2[6] = 1.3 V)	2.490 – P2[6]	2.586 – P2[6]	2.679 – P2[6]	V
		V_{AGND}	AGND	2 × Bandgap	2.523	2.594	2.669	V
		V_{REFLO}	Ref Low	2 × Bandgap – P2[6] (P2[6] = 1.3 V)	2.523 – P2[6]	2.598 – P2[6]	2.675 – P2[6]	V
	RefPower = medium Opamp bias = high	V_{REFHI}	Ref High	2 × Bandgap + P2[6] (P2[6] = 1.3 V)	2.493 – P2[6]	2.588 – P2[6]	2.682 – P2[6]	V
		V_{AGND}	AGND	2 × Bandgap	2.523	2.594	2.670	V
		V_{REFLO}	Ref Low	2 × Bandgap – P2[6] (P2[6] = 1.3 V)	2.523 – P2[6]	2.597 – P2[6]	2.675 – P2[6]	V
	RefPower = medium Opamp bias = low	V_{REFHI}	Ref High	2 × Bandgap + P2[6] (P2[6] = 1.3 V)	2.494 – P2[6]	2.589 – P2[6]	2.685 – P2[6]	V
		V_{AGND}	AGND	2 × Bandgap	2.523	2.595	2.671	V
		V_{REFLO}	Ref Low	2 × Bandgap – P2[6] (P2[6] = 1.3 V)	2.522 – P2[6]	2.596 – P2[6]	2.676 – P2[6]	V

Table 13. 3.3-V DC Analog Reference Specifications

Reference ARF_CR [5:3]	Reference Power Settings	Symbol	Reference	Description	Min	Typ	Max	Units
0b000	RefPower = high Opamp bias = high	V_{REFHI}	Ref High	$V_{DD}/2$ + Bandgap	$V_{DD}/2$ + 1.200	$V_{DD}/2$ + 1.290	$V_{DD}/2$ + 1.365	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.030	$V_{DD}/2$	$V_{DD}/2$ + 0.034	V
		V_{REFLO}	Ref Low	$V_{DD}/2$ – Bandgap	$V_{DD}/2$ – 1.346	$V_{DD}/2$ – 1.292	$V_{DD}/2$ – 1.208	V
	RefPower = high Opamp bias = low	V_{REFHI}	Ref High	$V_{DD}/2$ + Bandgap	$V_{DD}/2$ + 1.196	$V_{DD}/2$ + 1.292	$V_{DD}/2$ + 1.374	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.029	$V_{DD}/2$	$V_{DD}/2$ + 0.031	V
		V_{REFLO}	Ref Low	$V_{DD}/2$ – Bandgap	$V_{DD}/2$ – 1.349	$V_{DD}/2$ – 1.295	$V_{DD}/2$ – 1.227	V
	RefPower = medium Opamp bias = high	V_{REFHI}	Ref High	$V_{DD}/2$ + Bandgap	$V_{DD}/2$ + 1.204	$V_{DD}/2$ + 1.293	$V_{DD}/2$ + 1.369	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.030	$V_{DD}/2$	$V_{DD}/2$ + 0.030	V
		V_{REFLO}	Ref Low	$V_{DD}/2$ – Bandgap	$V_{DD}/2$ – 1.351	$V_{DD}/2$ – 1.297	$V_{DD}/2$ – 1.229	V
	RefPower = medium Opamp bias = low	V_{REFHI}	Ref High	$V_{DD}/2$ + Bandgap	$V_{DD}/2$ + 1.189	$V_{DD}/2$ + 1.294	$V_{DD}/2$ + 1.384	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.032	$V_{DD}/2$	$V_{DD}/2$ + 0.029	V
		V_{REFLO}	Ref Low	$V_{DD}/2$ – Bandgap	$V_{DD}/2$ – 1.353	$V_{DD}/2$ – 1.297	$V_{DD}/2$ – 1.230	V
0b001	RefPower = high Opamp bias = high	V_{REFHI}	Ref High	P2[4]+P2[6] (P2[4] = $V_{DD}/2$, P2[6] = 0.5 V)	P2[4] + P2[6] – 0.105	P2[4] + P2[6] – 0.008	P2[4] + P2[6] + 0.095	V
		V_{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V_{REFLO}	Ref Low	P2[4]–P2[6] (P2[4] = $V_{DD}/2$, P2[6] = 0.5 V)	P2[4] – P2[6] – 0.035	P2[4] – P2[6] + 0.006	P2[4] – P2[6] + 0.053	V
	RefPower = high Opamp bias = low	V_{REFHI}	Ref High	P2[4]+P2[6] (P2[4] = $V_{DD}/2$, P2[6] = 0.5 V)	P2[4] + P2[6] – 0.094	P2[4] + P2[6] – 0.005	P2[4] + P2[6] + 0.073	V
		V_{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V_{REFLO}	Ref Low	P2[4]–P2[6] (P2[4] = $V_{DD}/2$, P2[6] = 0.5 V)	P2[4] – P2[6] – 0.033	P2[4] – P2[6] + 0.002	P2[4] – P2[6] + 0.042	V
	RefPower = medium Opamp bias = high	V_{REFHI}	Ref High	P2[4]+P2[6] (P2[4] = $V_{DD}/2$, P2[6] = 0.5 V)	P2[4] + P2[6] – 0.094	P2[4] + P2[6] – 0.003	P2[4] + P2[6] + 0.075	V
		V_{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V_{REFLO}	Ref Low	P2[4]–P2[6] (P2[4] = $V_{DD}/2$, P2[6] = 0.5 V)	P2[4] – P2[6] – 0.035	P2[4] – P2[6]	P2[4] – P2[6] + 0.038	V
	RefPower = medium Opamp bias = low	V_{REFHI}	Ref High	P2[4]+P2[6] (P2[4] = $V_{DD}/2$, P2[6] = 0.5 V)	P2[4] + P2[6] – 0.095	P2[4] + P2[6] – 0.003	P2[4] + P2[6] + 0.080	V
		V_{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V_{REFLO}	Ref Low	P2[4]–P2[6] (P2[4] = $V_{DD}/2$, P2[6] = 0.5 V)	P2[4] – P2[6] – 0.038	P2[4] – P2[6]	P2[4] – P2[6] + 0.038	V
0b010	RefPower = high Opamp bias = high	V_{REFHI}	Ref High	V_{DD}	V_{DD} – 0.119	V_{DD} – 0.005	V_{DD}	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.028	$V_{DD}/2$	$V_{DD}/2$ + 0.029	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.004	V_{SS} + 0.022	V
	RefPower = high Opamp bias = low	V_{REFHI}	Ref High	V_{DD}	V_{DD} – 0.131	V_{DD} – 0.004	V_{DD}	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.028	$V_{DD}/2$	$V_{DD}/2$ + 0.028	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.003	V_{SS} + 0.021	V
	RefPower = medium Opamp bias = high	V_{REFHI}	Ref High	V_{DD}	V_{DD} – 0.111	V_{DD} – 0.003	V_{DD}	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.029	$V_{DD}/2$	$V_{DD}/2$ + 0.028	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.002	V_{SS} + 0.017	V
	RefPower = medium Opamp bias = low	V_{REFHI}	Ref High	V_{DD}	V_{DD} – 0.128	V_{DD} – 0.003	V_{DD}	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.029	$V_{DD}/2$	$V_{DD}/2$ + 0.029	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.002	V_{SS} + 0.019	V
0b011	All power settings. Not allowed for 3.3 V.	–	–	–	–	–	–	–

Table 13. 3.3-V DC Analog Reference Specifications (continued)

Reference ARF_CR [5:3]	Reference Power Settings	Symbol	Reference	Description	Min	Typ	Max	Units
0b100	All power settings. Not allowed for 3.3 V.	–	–	–	–	–	–	–
0b101	RefPower = high Opamp bias = high	V_{REFHI}	Ref High	P2[4] + Bandgap ($P2[4] = V_{DD}/2$)	P2[4] + 1.214	P2[4] + 1.291	P2[4] + 1.359	V
		V_{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V_{REFLO}	Ref Low	P2[4] – Bandgap ($P2[4] = V_{DD}/2$)	P2[4] – 1.335	P2[4] – 1.292	P2[4] – 1.200	V
	RefPower = high Opamp bias = low	V_{REFHI}	Ref High	P2[4] + Bandgap ($P2[4] = V_{DD}/2$)	P2[4] + 1.219	P2[4] + 1.293	P2[4] + 1.357	V
		V_{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V_{REFLO}	Ref Low	P2[4] – Bandgap ($P2[4] = V_{DD}/2$)	P2[4] – 1.335	P2[4] – 1.295	P2[4] – 1.243	V
	RefPower = medium Opamp bias = high	V_{REFHI}	Ref High	P2[4] + Bandgap ($P2[4] = V_{DD}/2$)	P2[4] + 1.222	P2[4] + 1.294	P2[4] + 1.356	V
		V_{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V_{REFLO}	Ref Low	P2[4] – Bandgap ($P2[4] = V_{DD}/2$)	P2[4] – 1.337	P2[4] – 1.296	P2[4] – 1.244	V
	RefPower = medium Opamp bias = low	V_{REFHI}	Ref High	P2[4] + Bandgap ($P2[4] = V_{DD}/2$)	P2[4] + 1.224	P2[4] + 1.295	P2[4] + 1.355	V
		V_{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V_{REFLO}	Ref Low	P2[4] – Bandgap ($P2[4] = V_{DD}/2$)	P2[4] – 1.339	P2[4] – 1.297	P2[4] – 1.244	V
0b110	RefPower = high Opamp bias = high	V_{REFHI}	Ref High	2 × Bandgap	2.510	2.595	2.655	V
		V_{AGND}	AGND	Bandgap	1.276	1.301	1.332	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.006	V_{SS} + 0.031	V
	RefPower = high Opamp bias = low	V_{REFHI}	Ref High	2 × Bandgap	2.513	2.594	2.656	V
		V_{AGND}	AGND	Bandgap	1.275	1.301	1.331	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.004	V_{SS} + 0.021	V
	RefPower = medium Opamp bias = high	V_{REFHI}	Ref High	2 × Bandgap	2.516	2.595	2.657	V
		V_{AGND}	AGND	Bandgap	1.275	1.301	1.331	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.003	V_{SS} + 0.017	V
	RefPower = medium Opamp bias = low	V_{REFHI}	Ref High	2 × Bandgap	2.520	2.595	2.658	V
		V_{AGND}	AGND	Bandgap	1.275	1.300	1.331	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.002	V_{SS} + 0.015	V
0b111	All power settings. Not allowed for 3.3 V.	–	–	–	–	–	–	–

DC Analog enCoRe III Block Specifications

The following table lists guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and –40 °C ≤ T_A ≤ 85 °C, or 3.15 V to 3.5 V and –40 °C ≤ T_A ≤ 85 °C, respectively. Typical parameters apply to 5 V and 3.3 V at 25 °C and are for design guidance only.

Table 14. DC Analog enCoRe III Block Specifications

Parameter	Description	Min	Typ	Max	Unit	Notes
R_{CT}	Resistor unit value (CT)	–	12.2	–	kΩ	–
C_{SC}	Capacitor unit value (SC)	–	80	–	fF	–

AC External Clock Specifications

The following tables list guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and –40 °C ≤ T_A ≤ 85 °C, or 3.15 V to 3.5 V and –40 °C ≤ T_A ≤ 85 °C, respectively. Typical parameters apply to 5 V and 3.3 V at 25 °C and are for design guidance only.

Table 22. AC External Clock Specifications

Parameter	Description	Min	Typ	Max	Unit	Notes
F_{OSCEXT}	Frequency for USB applications	23.94	24	24.06	MHz	USB operation in the extended Industrial temperature range (–40 °C ≤ T_A ≤ 85 °C) requires that the system clock is sourced from an external clock oscillator.
–	Duty cycle	47	50	53	%	–
–	Power-up to IMO switch	150	–	–	µs	–

AC Analog Output Buffer Specifications

The following tables list guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and –40 °C ≤ T_A ≤ 85 °C, or 3.15 V to 3.5 V and –40 °C ≤ T_A ≤ 85 °C, respectively. Typical parameters apply to 5 V and 3.3 V at 25 °C and are for design guidance only.

Table 23. 5 V AC Analog Output Buffer Specifications

Parameter	Description	Min	Typ	Max	Unit	Notes
T_{ROB}	Rising settling time to 0.1%, 1 V Step, 100-pF load Power = low Power = high	 – –	 – –	 2.5 2.5	 µs µs	–
T_{SOB}	Falling settling time to 0.1%, 1 V Step, 100-pF load Power = low Power = high	 – –	 – –	 2.2 2.2	 µs µs	–
SR_{ROB}	Rising slew rate (20% to 80%), 1 V Step, 100-pF load Power = low Power = high	 0.65 0.65	 – –	 – –	 V/µs V/µs	–
SR_{FOB}	Falling slew rate (80% to 20%), 1 V Step, 100-pF load Power = low Power = high	 0.65 0.65	 – –	 – –	 V/µs V/µs	–
BW_{OBSS}	Small signal bandwidth, 20 mV_{pp}, 3-dB BW, 100-pF load Power = low Power = high	 0.8 0.8	 – –	 – –	 MHz MHz	–
BW_{OBLS}	Large signal bandwidth, 1 V_{pp}, 3-dB BW, 100-pF load Power = low Power = high	 300 300	 – –	 – –	 kHz kHz	–

Table 24. 3.3 V AC Analog Output Buffer Specifications

Parameter	Description	Min	Typ	Max	Unit	Notes
T_{ROB}	Rising settling time to 0.1%, 1 V Step, 100-pF load Power = low Power = high	 – –	 – –	 3.8 3.8	 µs µs	–
T_{SOB}	Falling settling time to 0.1%, 1 V Step, 100-pF load Power = low Power = high	 – –	 – –	 2.6 2.6	 µs µs	–
SR_{ROB}	Rising slew rate (20% to 80%), 1 V Step, 100-pF load Power = low Power = high	 0.5 0.5	 – –	 – –	 V/µs V/µs	–
SR_{FOB}	Falling slew rate (80% to 20%), 1 V Step, 100-pF load Power = low Power = high	 0.5 0.5	 – –	 – –	 V/µs V/µs	–
BW_{OBSS}	Small signal bandwidth, 20 mV_{pp}, 3dB BW, 100-pF load Power = low Power = high	 0.7 0.7	 – –	 – –	 MHz MHz	–
BW_{OBLS}	Large signal bandwidth, 1 V_{pp}, 3dB BW, 100-pF load Power = low Power = high	 200 200	 – –	 – –	 kHz kHz	–

AC Programming Specifications

The following table lists guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and –40 °C ≤ T_A ≤ 85 °C, or 3.15 V to 3.5 V and –40 °C ≤ T_A ≤ 85 °C, respectively. Typical parameters apply to 5 V and 3.3 V at 25 °C and are for design guidance only.

Table 25. AC Programming Specifications

Parameter	Description	Min	Typ	Max	Unit	Notes
T_{RSCLK}	Rise time of SCLK	1	–	20	ns	–
T_{FSCLK}	Fall time of SCLK	1	–	20	ns	–
T_{SSCLK}	Data setup time to falling edge of SCLK	40	–	–	ns	–
T_{HSCLK}	Data hold time from falling edge of SCLK	40	–	–	ns	–
F_{SCLK}	Frequency of SCLK	0	–	8	MHz	–
T_{ERASEB}	Flash erase time (block)	–	10	–	ms	–
T_{WRITE}	Flash block write time	–	40	–	ms	–
T_{DSCLK}	Data out delay from falling edge of SCLK	–	–	45	ns	$V_{DD} > 3.6$
T_{DSCLK3}	Data out delay from falling edge of SCLK	–	–	50	ns	$3.15 \leq V_{DD} \leq 3.5$
$T_{ERASEALL}$	Flash erase time (bulk)	–	40	–	ms	Erase all blocks and protection fields at once.
$T_{PROGRAM\_HOT}$	Flash block erase + flash block write time	–	–	100	ms	0 °C ≤ T_J ≤ 100 °C
$T_{PROGRAM\_COLD}$	Flash block erase + flash block write time	–	–	200	ms	–40 °C ≤ T_J ≤ 0 °C

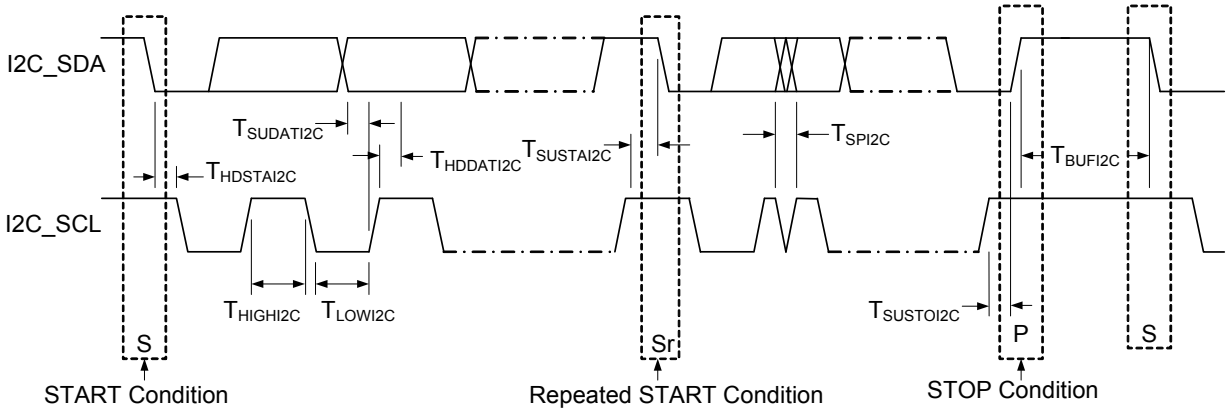
AC I²C Specifications

The following table lists guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and –40 °C ≤ T_A ≤ 85 °C, or 3.15 V to 3.5 V and –40 °C ≤ T_A ≤ 85 °C, respectively. Typical parameters apply to 5 V and 3.3 V at 25 °C and are for design guidance only.

Table 26. AC Characteristics of the I²C SDA and SCL Pins for V_{DD}

Parameter	Description	Standard-Mode		Fast-Mode		Unit	Notes
		Min	Max	Min	Max		
F_{SCLI2C}	SCL clock frequency	0	100	0	400	kHz	–
$T_{HDSTAI2C}$	Hold time (repeated) START condition. After this period, the first clock pulse is generated.	4.0	–	0.6	–	µs	–
T_{LOWI2C}	LOW period of the SCL clock	4.7	–	1.3	–	µs	–
$T_{HIGHI2C}$	HIGH period of the SCL clock	4.0	–	0.6	–	µs	–
$T_{SUSTAI2C}$	Setup time for a repeated START condition	4.7	–	0.6	–	µs	–
$T_{HDDATI2C}$	Data hold time	0	–	0	–	µs	–
$T_{SUDATI2C}$	Data setup time	250	–	100[17]	–	ns	–
$T_{SUSTOI2C}$	Setup time for STOP condition	4.0	–	0.6	–	µs	–
T_{BUFI2C}	Bus free time between a STOP and START condition	4.7	–	1.3	–	µs	–
T_{SPI2C}	Pulse width of spikes are suppressed by the input filter.	–	–	0	50	ns	–

Figure 7. Definition for Timing for Fast-/Standard-Mode on the I²C Bus



Note

17. A Fast-Mode I²C-bus device can be used in a Standard-Mode I²C-bus system, but the requirement $T_{SUDATI2C} \geq 250$ ns must then be met. This automatically is the case if the device does not stretch the LOW period of the SCL signal. If such device does stretch the LOW period of the SCL signal, it must output the next data bit to the SDA line $t_{rmax} + T_{SUDATI2C} = 1000 + 250 = 1250$ ns (according to the Standard-Mode I²C-bus specification) before the SCL line is released.

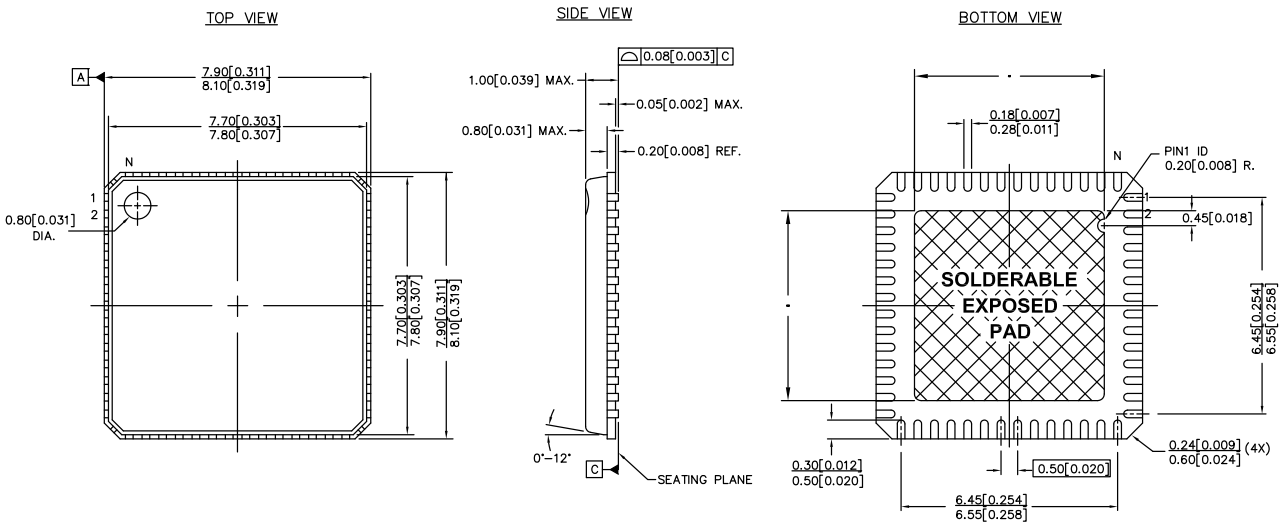
Packaging Information

This section illustrates the package specification for the CY7C64215 enCoRe III, along with the thermal impedance for the package.

Important Note Emulation tools may require a larger area on the target PCB than the chip's footprint. For a detailed description of the emulation tools' dimensions, refer to the emulator pod drawings at http://www.cypress.com.

Package Diagrams

Figure 8. 56-pin QFN (8 × 8 × 1.0 mm) 4.5 × 5.21 E-Pad (Subcon Punch Type Package) Package Outline, 001-12921



NOTES:

1. ▨ HATCH AREA IS SOLDERABLE EXPOSED METAL.
2. REFERENCE JEDEC#: MO–220
3. PACKAGE WEIGHT: 0.162g
4. ALL DIMENSIONS ARE IN MM [MIN/MAX]
5. PACKAGE CODE

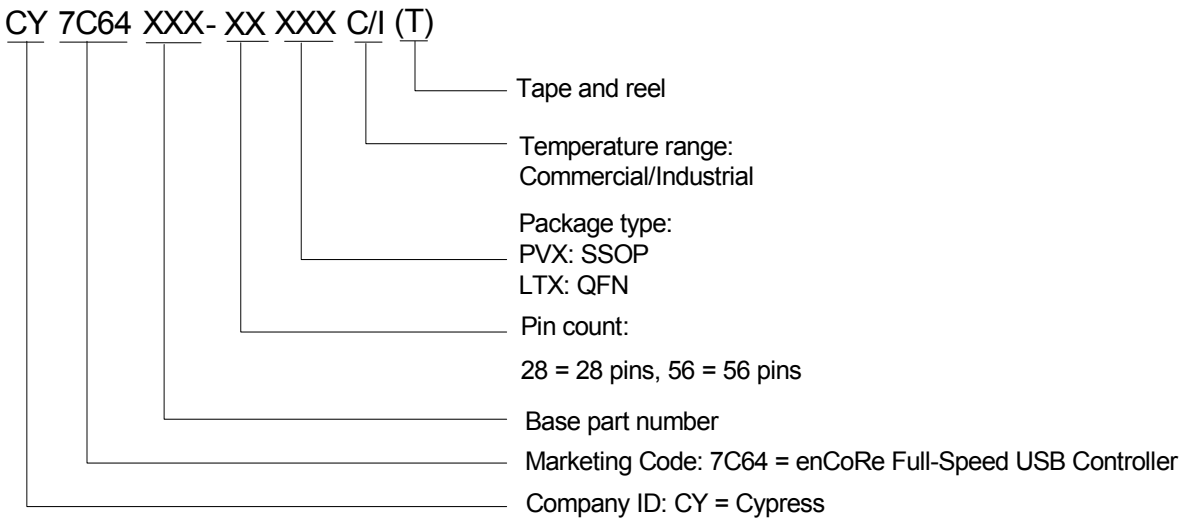
PART #	DESCRIPTION
LF56A	STANDARD
LY56A	PB–FREE

001-12921 *C

Ordering Information

Package	Ordering Code	Flash Size	SRAM (Bytes)	Temperature Range
28-pin SSOP	CY7C64215-28PVXC	16K	1K	Commercial, 0 °C to 70 °C
28-pin SSOP (Tape and Reel)	CY7C64215-28PVXCT	16K	1K	Commercial, 0 °C to 70 °C
28-pin SSOP	CY7C64215-28PVXI	16 K	1K	Industrial, –40 °C to 85 °C
28-pin SSOP (Tape and Reel)	CY7C64215-28PVXIT	16 K	1K	Industrial, –40 °C to 85 °C
56-pin QFN (Sawn)	CY7C64215-56LTXC	16K	1K	Commercial, 0 °C to 70 °C
56-pin QFN (Sawn) (Tape and Reel)	CY7C64215-56LTXCT	16K	1K	Commercial, 0 °C to 70 °C
56-pin QFN (Sawn)	CY7C64215-56LTXI	16K	1K	Industrial, –40 °C to 85 °C
56-pin QFN (Sawn) (Tape and Reel)	CY7C64215-56LTXIT	16K	1K	Industrial, –40 °C to 85 °C

Ordering Code Definitions



noise	1. A disturbance that affects a signal and that may distort the information carried by the signal. 2. The random variations of one or more characteristics of any entity such as voltage, current, or data.
oscillator	A circuit that may be crystal controlled and is used to generate a clock frequency.
parity	A technique for testing transmitting data. Typically, a binary digit is added to the data to make the sum of all the digits of the binary data either always even (even parity) or always odd (odd parity).
phase-locked loop (PLL)	An electronic circuit that controls an ***oscillator*** so that it maintains a constant phase angle relative to a reference signal.
pinouts	The pin number assignment: the relation between the logical inputs and outputs of the PSoC device and their physical counterparts in the printed circuit board (PCB) package. Pinouts involve pin numbers as a link between schematic and PCB design (both being computer generated files) and may also involve pin names.
port	A group of pins, usually eight.
power on reset (POR)	A circuit that forces the PSoC device to reset when the voltage is lower than a pre-set level. This is one type of hardware reset.
PSoC®	Cypress Semiconductor's PSoC® is a registered trademark and Programmable System-on-Chip™ is a trademark of Cypress.
PSoC Designer™	The software for Cypress' Programmable System-on-Chip technology.
pulse width modulator (PWM)	An output in the form of duty cycle which varies as a function of the applied measurand
RAM	An acronym for random access memory. A data-storage device from which data can be read out and new data can be written in.
register	A storage device with a specific capacity, such as a bit or byte.
reset	A means of bringing a system back to a know state. See hardware reset and software reset.
ROM	An acronym for read only memory. A data-storage device from which data can be read out, but new data cannot be written in.
serial	1. Pertaining to a process in which all events occur one after the other. 2. Pertaining to the sequential or consecutive occurrence of two or more related activities in a single device or channel.
settling time	The time it takes for an output signal or value to stabilize after the input has changed from one value to another.
shift register	A memory storage device that sequentially shifts a word either left or right to output a stream of serial data.
slave device	A device that allows another device to control the timing for data exchanges between two devices. Or when devices are cascaded in width, the slave device is the one that allows another device to control the timing of data exchanges between the cascaded devices and an external interface. The controlling device is called the master device.
SRAM	An acronym for static random access memory. A memory device allowing users to store and retrieve data at a high rate of speed. The term static is used because, after a value has been loaded into an SRAM cell, it remains unchanged until it is explicitly altered or until power is removed from the device.

■ **Fix Status**

There is no planned silicon fix; use workaround.

2. Invalid flash reads may occur if V_{DD} is pulled to –0.5 V just before power on

■ **Problem Definition**

When V_{DD} of the device is pulled below ground just before power on, the first read from each 8-KB flash page may be corrupted. This issue does not affect flash page 0 because it is the selected page upon reset.

■ **Parameters Affected**

When V_{DD} is pulled below ground before power on, an internal flash reference may deviate from its nominal voltage. The reference deviation tends to result in the first flash read from that page returning 0xFF. During the first read from each page, the reference is reset resulting in all future reads returning the correct value. A short delay of 5 µs before the first real read provides time for the reference voltage to stabilize.

■ **Trigger Condition**

N/A

■ **Scope of Impact**

N/A

■ **Workaround**

To prevent an invalid flash read, a dummy read from each flash page must occur before use of the pages. A delay of 5 µs must occur after the dummy read and before a real read. The dummy reads occur as soon as possible and must be located in flash page 0 before a read from any other flash page. An example for reading a byte of memory from each flash page is listed below. Place it in *boot.tpl* and *boot.asm* immediately after the ‘start:’ label.

```
// dummy read from each 8K Flash page
// page 1
movA, 0x20       // MSB
movX, 0x00       // LSB
romx
// wait at least 5 µs
movX, 14
loop1:
decX
jnzloop1
```

■ **Fix Status**

There is no planned silicon fix; use workaround.

3. PMA Index Register fails to auto-increment with CPU_Clock set to SysClk/1 (24 MHz)

■ **Problem Definition**

When the device operates at 4.75 V to 5.25 V and the CPU_Clock is set to SysClk/1 (24 MHz), the USB PMA Index Register may fail to increment automatically when used in an OUT endpoint configuration at full-speed. When the application program attempts to use the bReadOutEP() function, the first byte in the PMA buffer is always returned.

■ **Parameters Affected**

An internal flip-flop hold problem is associated with the index register increment function. All reads of the associated RAM originate from the first byte. The hold problem has no impact on other circuits or functions within the device.

■ **Trigger Condition**

N/A

■ **Scope of Impact**

N/A

■ **WORKAROUND**

To make certain that the index register properly increments, set the CPU_Clock to SysClk/2 (12 MHz) during the read of the PMA buffer. An example for the clock adjustment method follows:

PSoC Designer 4.3 User Module workaround: PSoC Designer Release 4.3 and subsequent releases include a revised full-speed USB User Module with the revised firmware workaround included (see the following example).

24-Mhz read PMA workaround

```
;;
M8C_SetBank1
mov A, reg[OSC_CR0]
push A
and A, 0xf8 ;clear the clock bits (briefly chg the cpu_clk to 3Mhz)
or A, 0x02 ;will set clk to 12Mhz

mov reg[OSC_CR0],A ;clk is now set at 12Mhz
M8C_SetBank0
.loop:
   mov A, reg[PMA0_DR] ; Get the data from the PMA space
   mov [X], A ; save it in data array
   inc X ; increment the pointer
   dec [USB_APITemp+1] ; decrement the counter
   jnz .loop ; wait for count to zero out
;;
;; 24Mhz read PMA workaround (back to previous clock speed)
;;
pop A ;recover previous reg[OSC_CR0] value
M8C_SetBank1
mov reg[OSC_CR0],A ;clk is now set at previous value
M8C_SetBank0
;;
;; end 24Mhz read PMA workaround
```

■ **Fix Status**

There is no planned silicon fix; use workaround.

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